



STD1NK60 - STD1NK60-1 STQ1HNK60R - STN1HNK60

N-CHANNEL 600V - 8Ω - 1A DPAK/TO-92/IPAK/SOT-223

SuperMESH™ MOSFET

Table 1: General Features

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _W
STD1NK60	600 V	< 8.5 Ω	1 A	30 W
STD1NK60-1	600 V	< 8.5 Ω	1 A	30 W
STQ1HNK60R	600 V	< 8.5 Ω	0.4 A	3 W
STN1HNK60	600 V	< 8.5 Ω	0.4 A	3.3 W

- TYPICAL R_{DS(on)} = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ESD IMPROVED CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

APPLICATIONS

- LOW POWER BATTERY CHARGERS
- SWITCH MODE LOW POWER SUPPLIES(SMPS)
- LOW POWER, BALLAST, CFL (COMPACT FLUORESCENT LAMPS)

Figure 1: Package

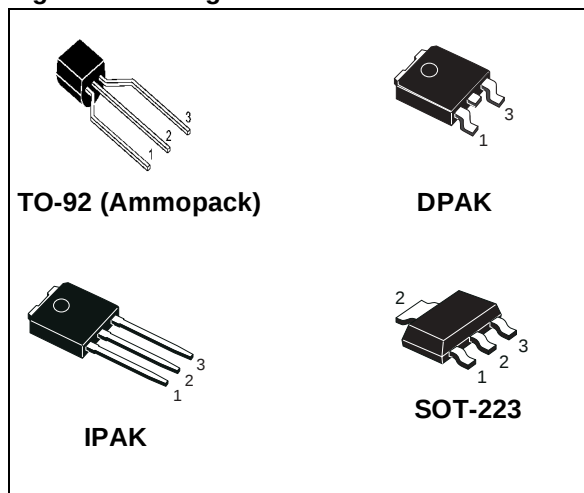


Figure 2: Internal Schematic Diagram

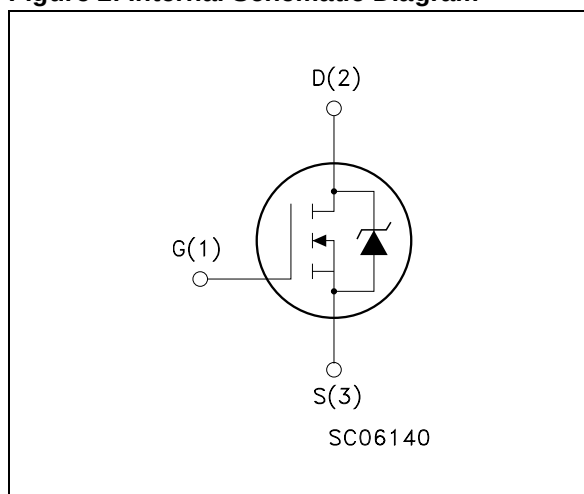


Table 2: Order Codes

Part Number	Marking	Package	Packaging
STD1NK60T4	D1NK60	DPAK	TAPE & REEL
STD1NK60-1	D1NK60	IPAK	TUBE
STQ1HNK60R	1HNK60R	TO-92	BULK
STQ1HNK60R-AP	1HNK60R	TO-92	AMMOPAK
STN1HNK60	N1HNK60	SOT-223	TAPE & REEL

Rev. 3

STD1NK60 - STD1NK60-1 - STQ1HNK60R - STN1HNK60

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value			Unit
		DPAK / IPAK	TO-92	SOT-223	
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	600			V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	600			V
V_{GS}	Gate- source Voltage	± 30			V
I_D	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	1.0	0.4	0.4	A
I_D	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	0.63	0.25	0.25	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	4	1.6	1.6	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	30	3	3.3	W
	Derating Factor	0.24	0.025	0.025	W/ $^\circ\text{C}$
$dv/dt(1)$	Peak Diode Recovery voltage slope	3			V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150			$^\circ\text{C}$

($\bullet$) Pulse width limited by safe operating area

(1) $I_{SD} \leq 1.0\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{jMAX}$.

Table 4: Thermal Data

		DPAK/IPAK	TO-92	SOT-223	Unit
$R_{thj-case}$	Thermal Resistance Junction-case Max	4.16	--	--	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	100	120	37.87 (#)	$^\circ\text{C}/\text{W}$
$R_{thj-lead}$	Thermal Resistance Junction-lead Max	--	40	--	$^\circ\text{C}/\text{W}$
T_l	Maximum Lead Temperature For Soldering Purpose	275	260		$^\circ\text{C}$

(#) When mounted on FR-4 board of 1 in^2 , 2oz Cu, $t < 10\text{ sec}$

Table 5: Avalanche Characteristics

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	1	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	25	mJ

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

Table 6: On/Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1\text{mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^\circ\text{C}$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2.25	3	3.7	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 0.5\text{ A}$		8	8.5	Ω

ELECTRICAL CHARACTERISTICS (CONTINUED)

Table 7: Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	$V_{DS} = 15\text{ V}$, $I_D = 0.5\text{ A}$		1		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		156 23.5 3.8		pF pF pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time	$V_{DD} = 300\text{ V}$, $I_D = 0.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 21)		6.5 5 19 25		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480\text{ V}$, $I_D = 1\text{ A}$, $V_{GS} = 10\text{ V}$, $R_G = 4.7\ \Omega$ (see, Figure 23)		7 1.1 3.7	10	nC nC nC

Table 8: Source Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM} (2)	Source-drain Current Source-drain Current (pulsed)				1 4	A A
V_{SD} (1)	Forward On Voltage	$I_{SD} = 1.0\text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 1.0\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$, $T_j = 25^\circ\text{C}$ (see test circuit, Figure 22)		140 240 3.3		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 1.0\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 25\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 22)		229 377 3.3		ns μC A

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(2) Pulse width limited by safe operating area.

Figure 3: Safe Operating Area For SOT-223

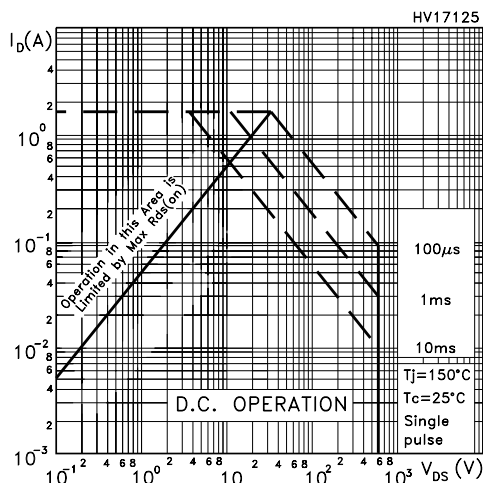


Figure 4: Safe Operating Area For DPAK/IPAK

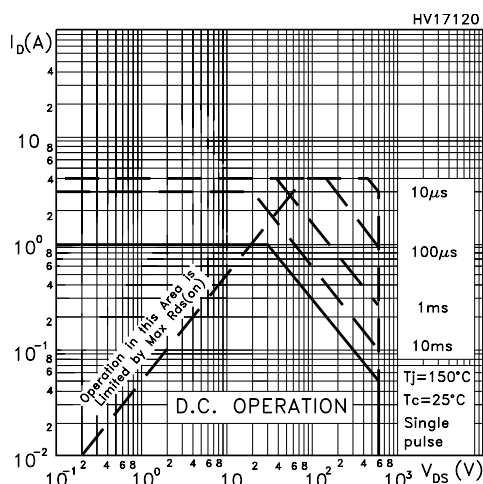


Figure 5: Safe Operating Area For TO-92

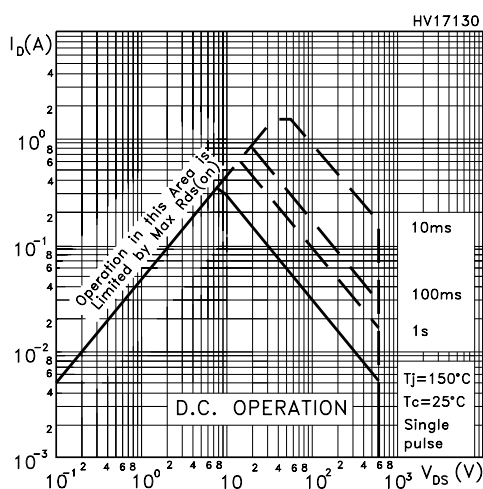


Figure 6: Thermal Impedance For SOT-223

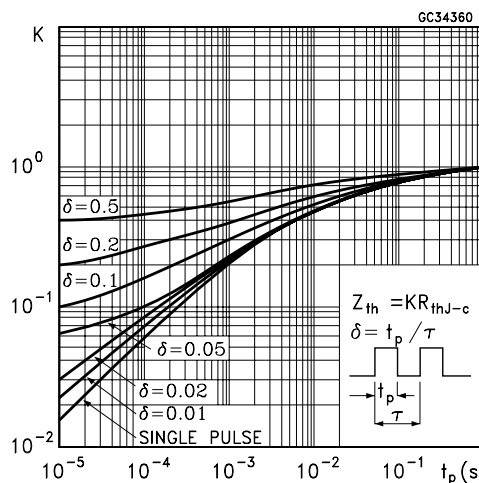


Figure 7: Thermal Impedance For DPAK/IPAK

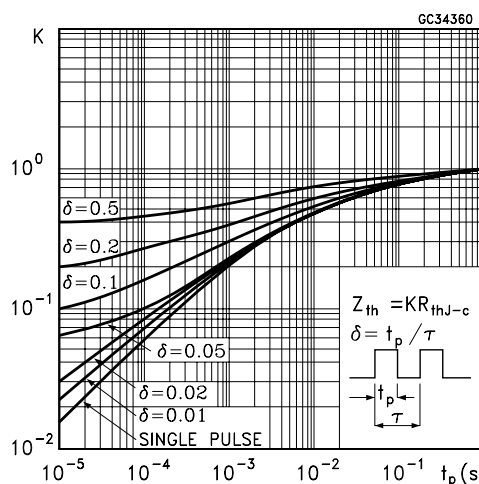


Figure 8: Thermal Impedance For TO-92

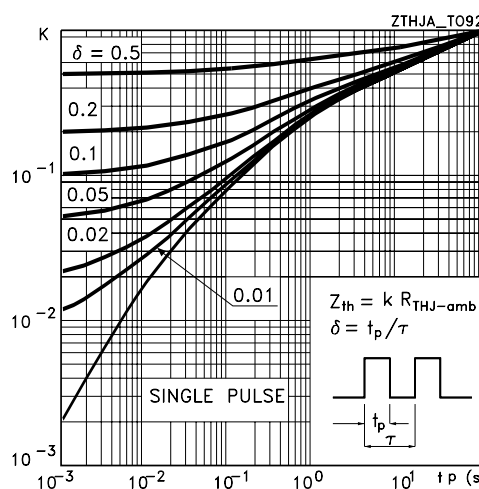


Figure 9: Output Characteristics

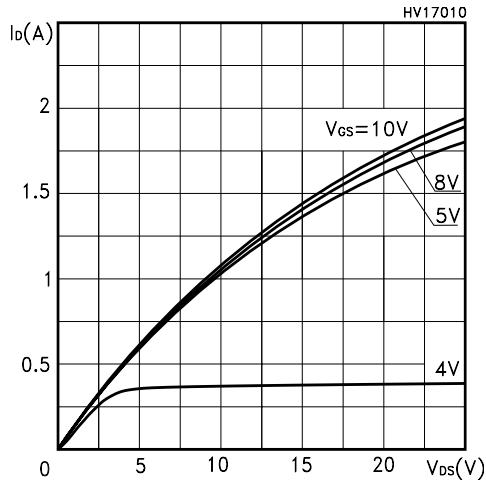


Figure 10: Transconductance

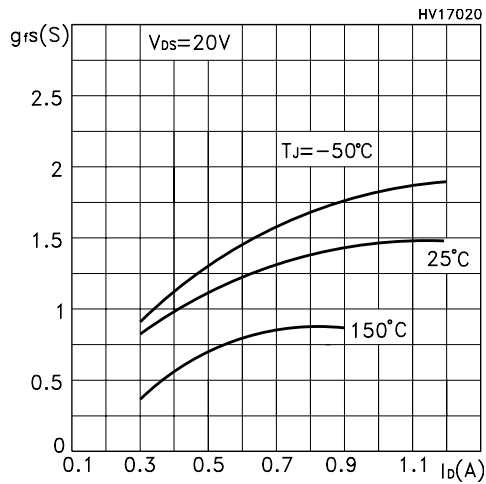


Figure 11: Capacitance Variations

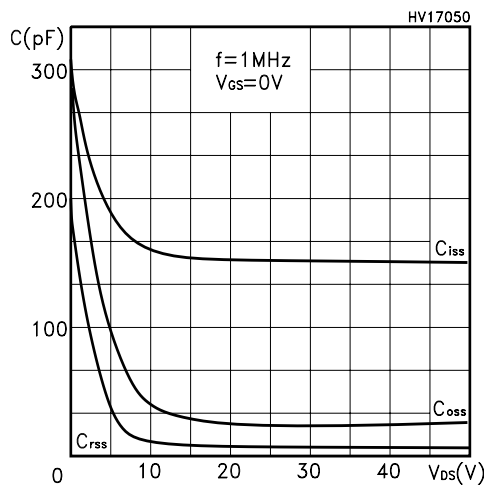


Figure 12: Transfer Characteristics

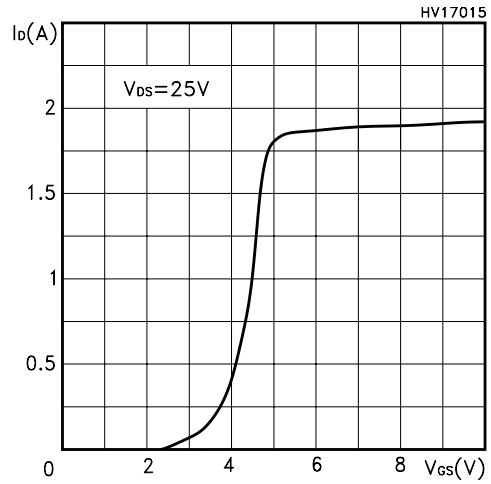


Figure 13: Gate Charge vs Gate-source Voltage

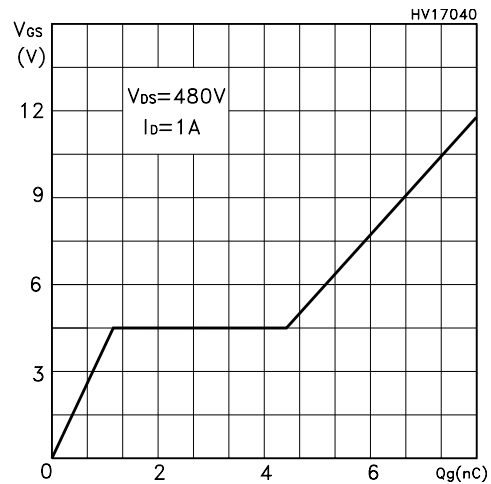


Figure 14: Static Drain-source On Resistance

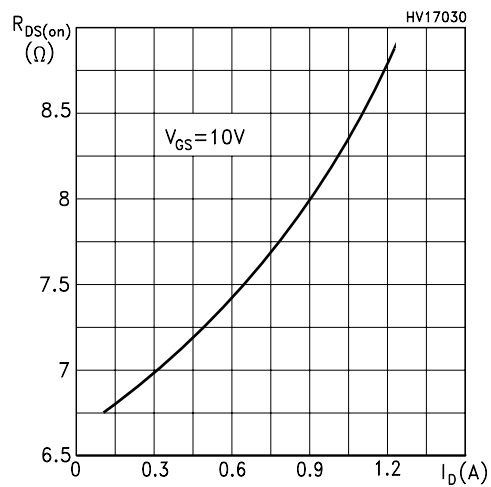


Figure 15: Normalized Gate Threshold Voltage vs Temperature

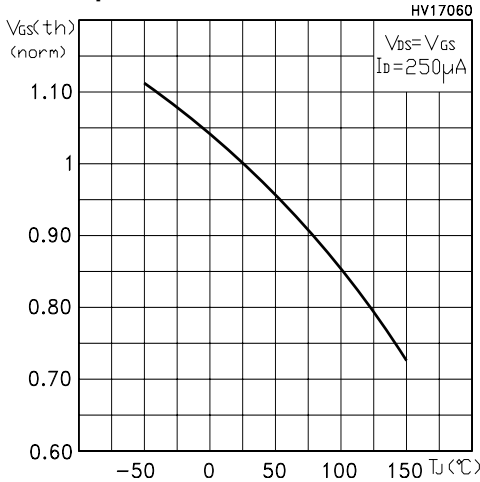


Figure 16: Source-Drain Forward Characteristics

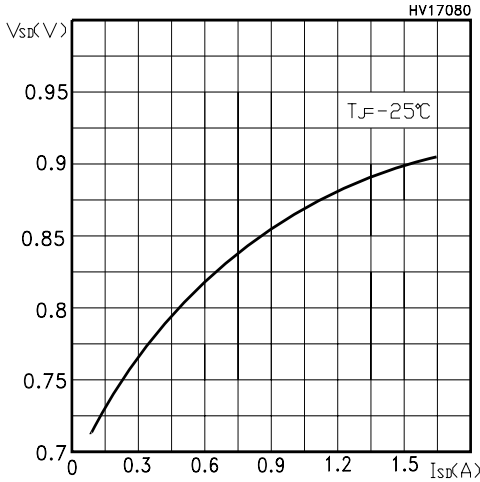


Figure 17: Maximum Avalanche Energy vs Temperature

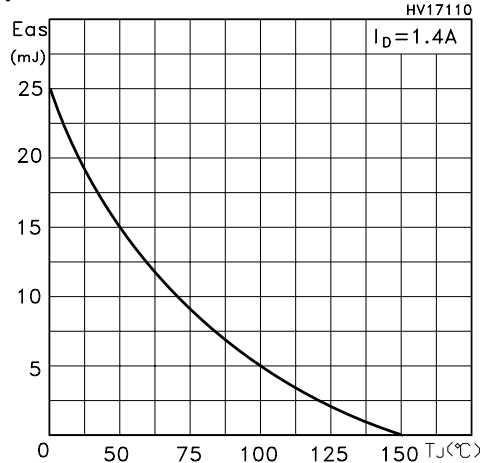


Figure 18: Normalized On Resistance vs Temperature

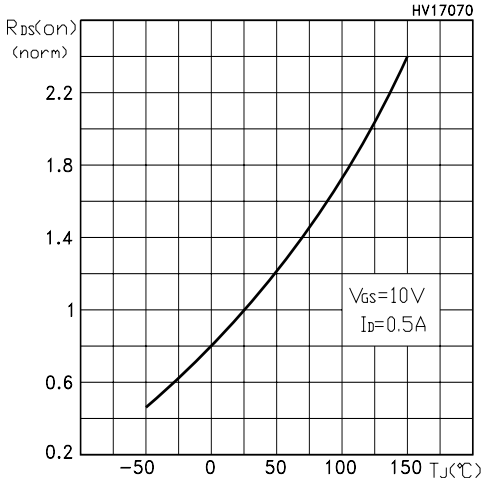


Figure 19: Normalized BV_{DSS} vs Temperature

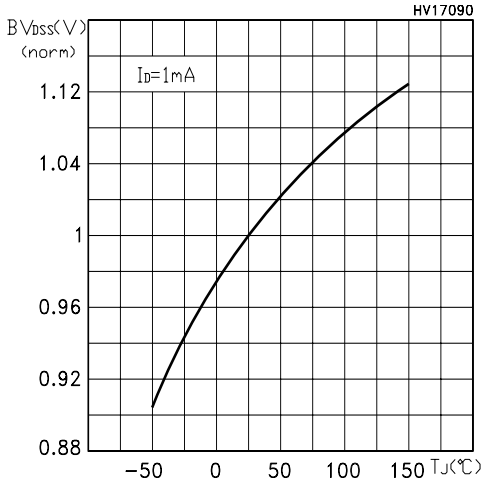


Figure 20: Max Id Current vs Tc

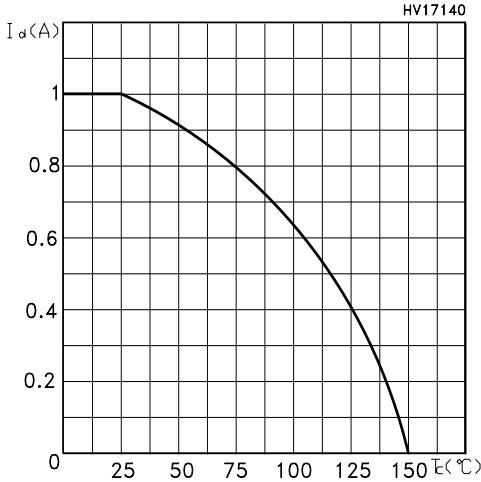


Figure 21: Switching Times Test Circuit For Resistive Load

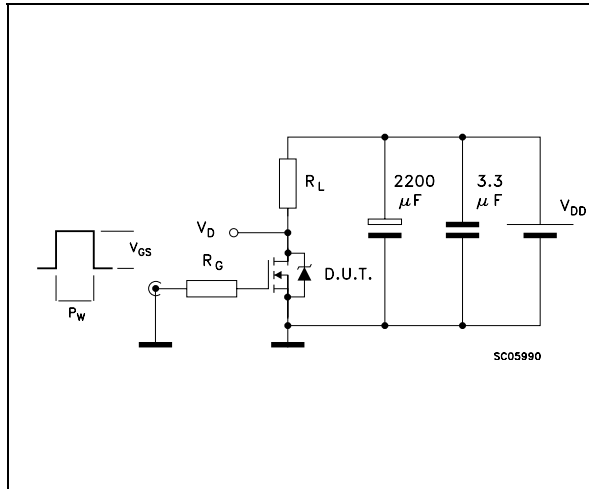


Figure 22: Test Circuit For Inductive Load Switching and Diode Recovery Times

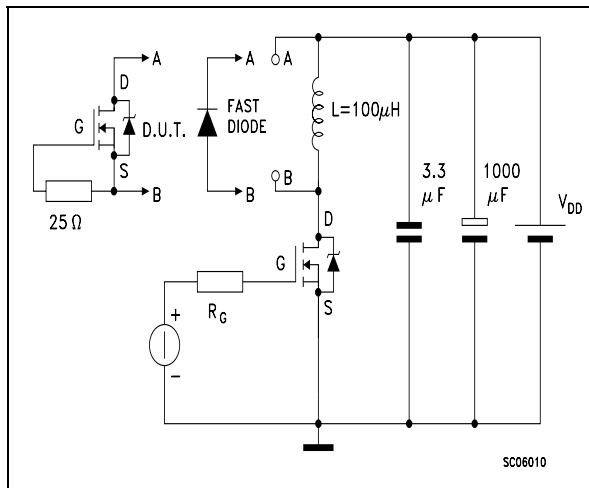
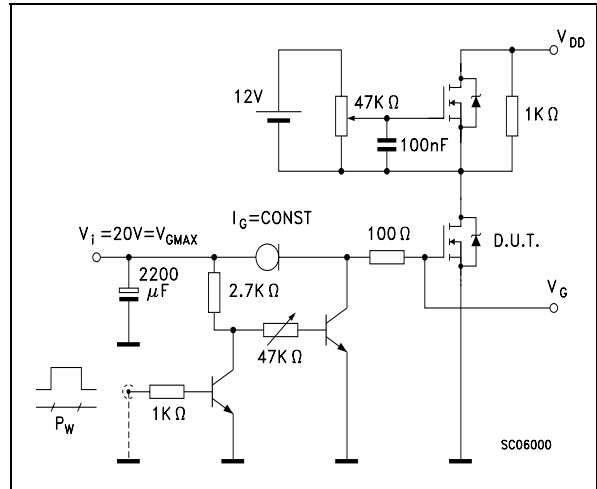
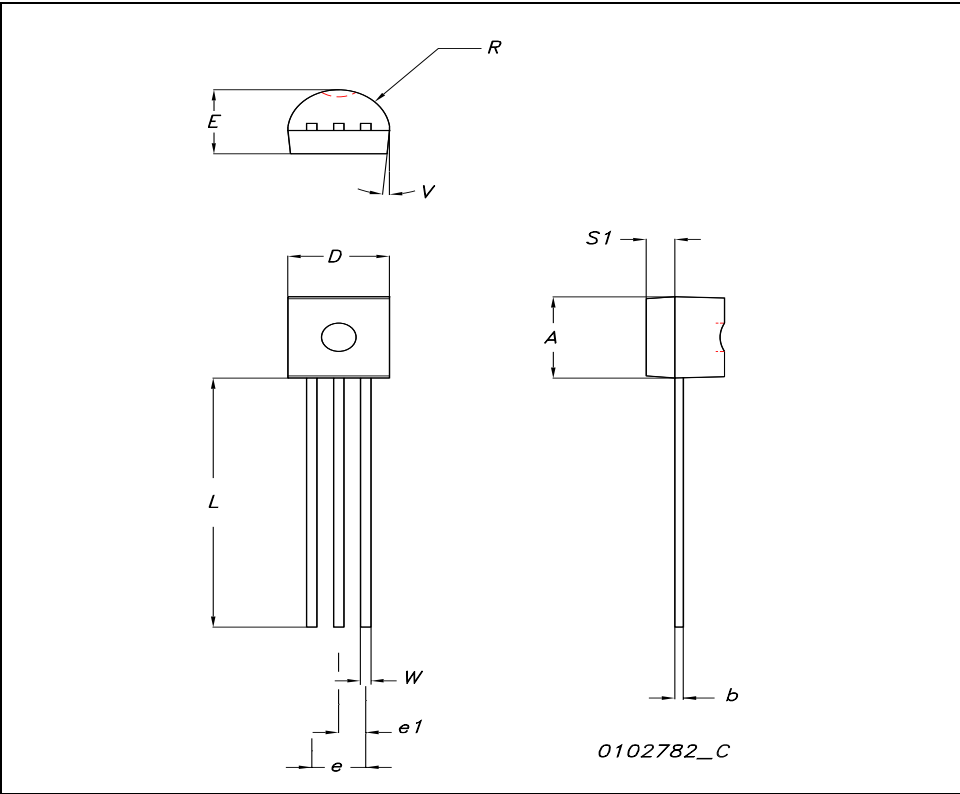


Figure 23: Gate Charge Test Circuit



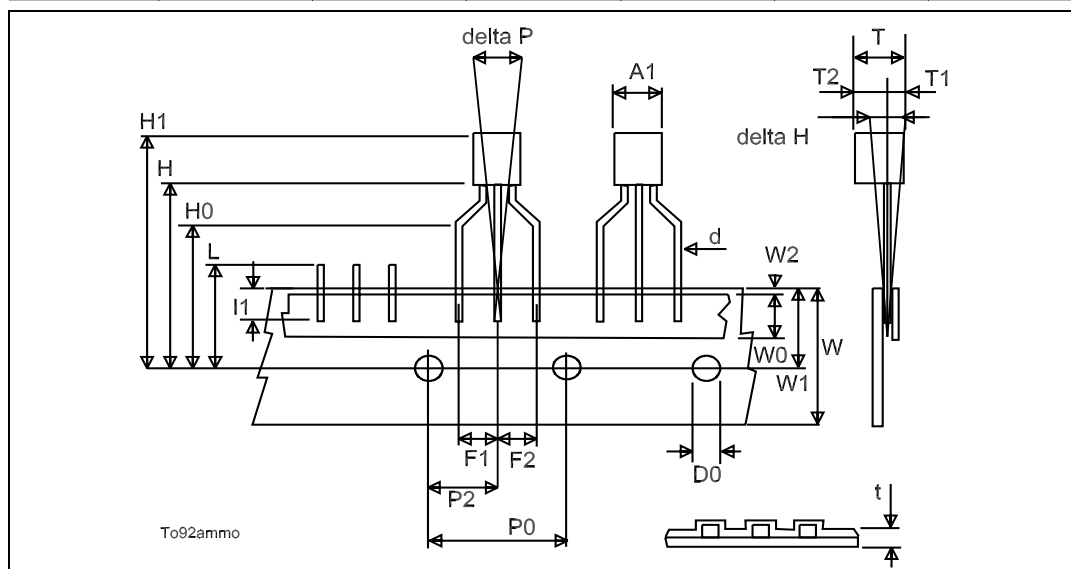
TO-92 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.194
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.094		0.105
e1	1.14		1.40	0.044		0.055
L	12.70		15.49	0.50		0.610
R	2.16		2.41	0.085		0.094
S1	0.92		1.52	0.036		0.060
W	0.41		0.56	0.016		0.022
V		5°			5°	



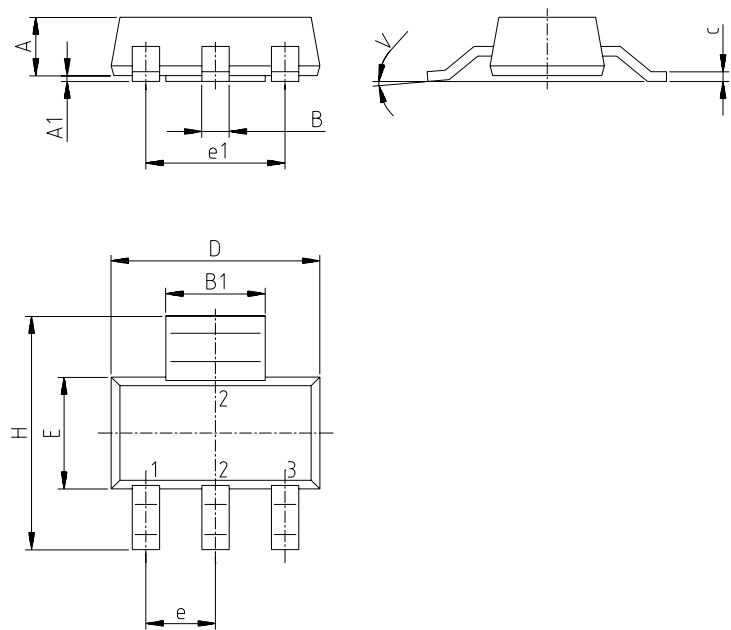
TO-92 AMMOPACK

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A1	4.45		4.95	0.170		0.194
T	3.30		3.94	0.130		0.155
T1			1.6			0.06
T2			2.3			0.09
d	0.41		0.56	0.016		0.022
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
l1	3			0.11		
delta P	-1		1	-0.04		0.04



SOT-223 MECHANICAL DATA

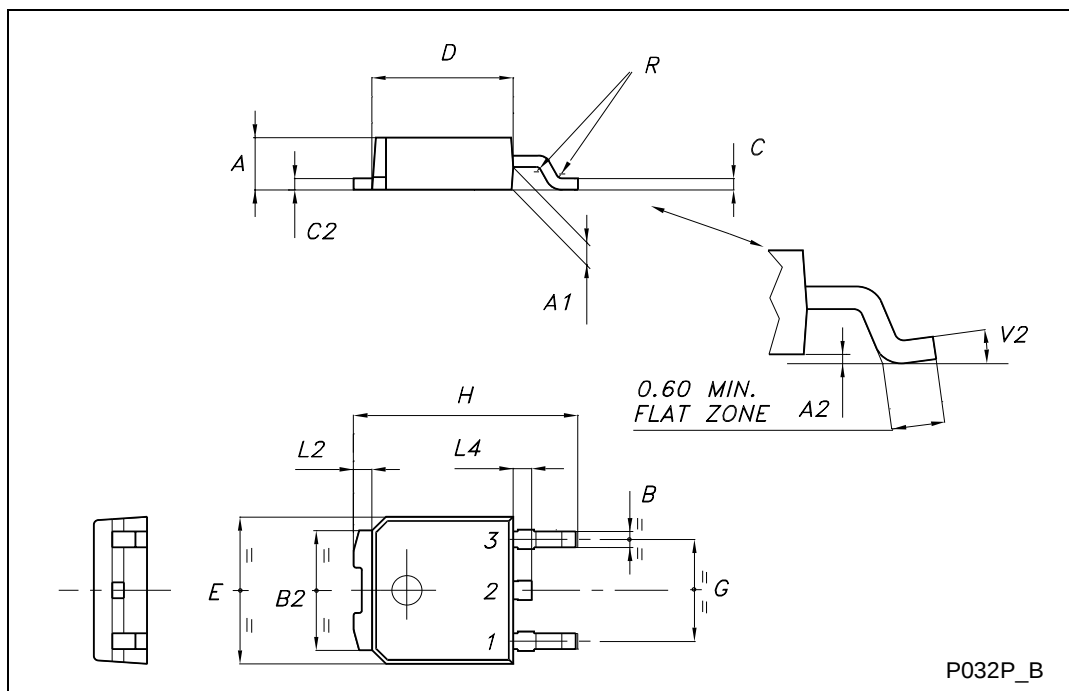
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.80			0.071
B	0.60	0.70	0.80	0.024	0.027	0.031
B1	2.90	3.00	3.10	0.114	0.118	0.122
c	0.24	0.26	0.32	0.009	0.010	0.013
D	6.30	6.50	6.70	0.248	0.256	0.264
e		2.30			0.090	
e1		4.60			0.181	
E	3.30	3.50	3.70	0.130	0.138	0.146
H	6.70	7.00	7.30	0.264	0.276	0.287
V			10°			10°
A1		0.02				



P008B

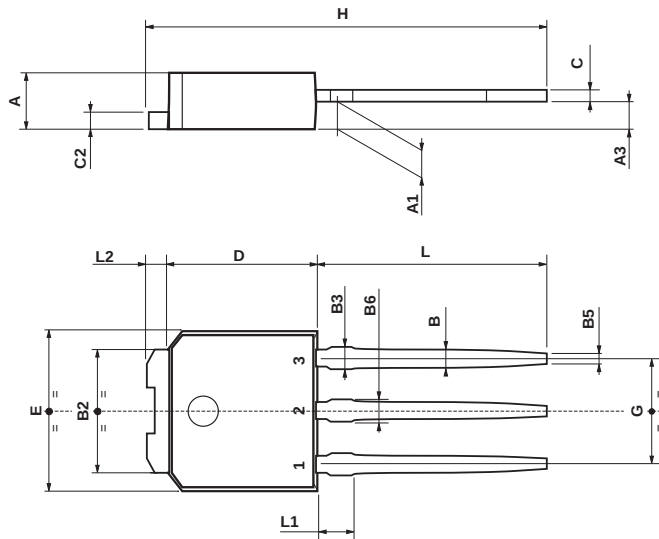
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



0068771-E

Technical drawing of a mechanical part with dimensions in millimeters. The drawing shows a front view and a top view. The front view is a rectangle with a width of 6.7 mm and a height of 6.7 mm. The top view is a rectangle with a width of 6.7 mm and a height of 1.6 mm. The dimensions are labeled as follows:

- Front view width: 6.7 mm
- Front view height: 6.7 mm
- Top view width: 6.7 mm
- Top view height: 1.6 mm
- Distance between front and top view: 1.8 mm
- Distance between top and bottom view: 3.0 mm
- Distance between front and bottom view: 1.6 mm
- Distance between top and bottom view: 2.3 mm

All dimensions are in millimeters

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

REEL MECHANICAL DATA

Technical drawing of a reel showing dimensions A, B, C, D, G, N, and T. A 40 mm min. access hole is located at the slot position. The tape slot in the core for tape start is 2.5 mm min. width. G is measured at the hub.

TAPE MECHANICAL DATA

Technical drawing of a tape showing dimensions A0, B0, B1, D, D1, E, F, K0, P0, P1, P2, R, and W. The drawing also shows the TOP COVER TAPE, the center line of the cavity, and the user direction of feed. The bending radius is R min.

BASE QTY 2500 **BULK QTY** 2500

Table 9: Revision History

Date	Revision	Description of Changes
22-Nov-2004	2	Added SOT-223 Package and new stylesheet
14-Feb-2006	3	Modified marking on Table 2

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